

N-Channel 80 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
80	2.8 at V _{GS} = 10 V	100	96 nC			

Din-Tek

SEMICONDUCTOR

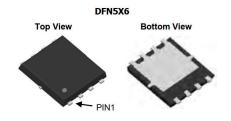
FEATURES

- DT-SJ Power MOSFET
- 100 % R_g and UIS Tested

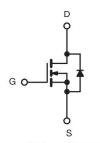


APPLICATIONS

- Primary Side Switch
- Isolated DC/DC Converters
- Full Bridge
- Synchonous Rectification







N-Channel MO	SEE	
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ABSOLUTE MAXIMUM RATINGS (T	_A = 25 °C, unle	ess otherwise i	noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	80	V	
Gate-Source Voltage		V _{GS}	± 20		
	T _C = 25 °C		100 ^a		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C		80 ^a		
Continuous Brain Guiterit (1) = 100 G)	T _A = 25 °C	l _D	37 ^{b,c}		
	T _A = 70 °C		29b,c	Α	
Pulsed Drain Current (t = 300 µs)		I _{DM}	400	A	
Continuous Source-Drain Diode Current	T _C = 25 °C	1	100 ^a		
Continuous Source-Diairi Diode Current	T _A = 25 °C	l _S	9.9 ^{b, c}		
Single Pulse Avalanche Current	L = 0.5 mH	I _{AS}	75		
Single Pulse Avalanche Energy	L = 0.5 IIII	E _{AS}	389	mJ	
	T _C = 25 °C		225	W	
Maximum Power Dissipation	T _C = 70 °C]	158		
Maximum Tower Dissipation	T _A = 25 °C	P_{D}	8 ^{b, c}	VV	
	T _A = 70 °C		5.6 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260	J	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	14	23	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	0.5	1.0		

- Notes:
 a. Package limited.
 b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile. The DFN5X6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

 e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 65 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$		-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 = 2504	-	37	=	mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	- 5.6	-	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	-	4	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
	I _{DSS} -	V _{DS} =80 V, V _{GS} = 0 V	-	-	1	μA
Zero Gate Voltage Drain Current		$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	100	-	-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	2.8	3.5	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 64 V, I _D = 20 A	=	93	-	S
Dynamic ^b				•	•	•
Input Capacitance	C _{iss}		-	5490	-	pF
Output Capacitance	C _{oss}	V_{DS} = 40V, V_{GS} = 0 V, f = 1 MHz	-	879	-	
Reverse Transfer Capacitance	C _{rss}		-	36	-	
Total Gate Charge	Q _q		-	96	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} = 40 V, V_{GS} = 10 V, I_{D} = 10 A	-	29	-	
Gate-Drain Charge	Q _{gd}		=	41	_	
Output Charge	Q _{oss}	V_{DS} = 40 V, V_{GS} = 0 V	-	70	-	
Gate Resistance	R _g	f = 1 MHz	-	1	-	Ω
Turn-On Delay Time	t _{d(on)}		-	15	-	-
Rise Time	t _r	$V_{DD} = 40 \text{ V}, R_L = 4 \Omega$	-	10	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	45	-	
Fall Time	t _f		-	19	-	1
Turn-On Delay Time	t _{d(on)}		-	18	-	ns
Rise Time	t _r	V_{DD} = 40 V, R_L = 4 Ω	-	16	_	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 20$ A, V_{GEN} = 7.5 V, R_g = 1 Ω	-	55	-	
Fall Time	t _f		-	11	-	
Drain-Source Body Diode Characteristi	cs					
Continuous Source-Drain Diode Current	Is	$T_C = 25 ^{\circ}C$	-	-	100	A
Pulse Diode Forward Current ^a	I _{SM}		=	-	400	
Body Diode Voltage	V _{SD}	I _S = 5 A	-	-	1.2	V
Body Diode Reverse Recovery Time	t _{rr}		-	36	1-1	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 10 A, dl/dt = 100 A/μs, T _J = 25 °C		156	-	nC
Reverse Recovery Fall Time	t _a	1 _F = 10 A, αι/αι = 100 A/μs, 1 _J = 25 °C	·-	22	_	
Reverse Recovery Rise Time t _b			25	-	ns	

Notes:

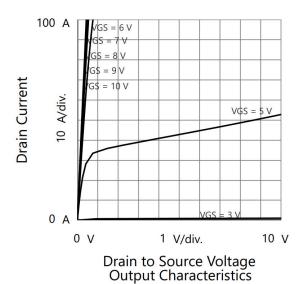
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

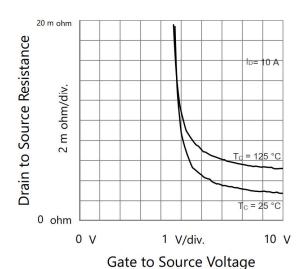
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

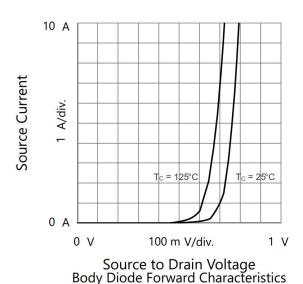


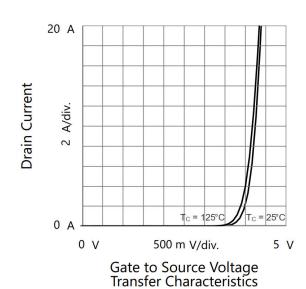
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

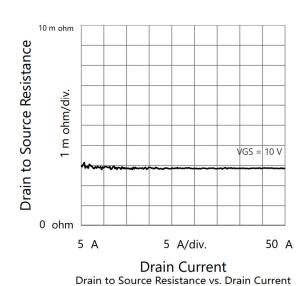


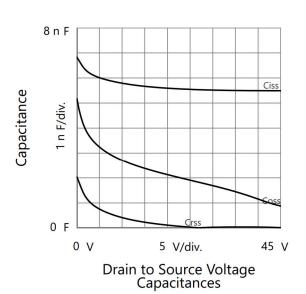


Drain to Source Resistance vs. Gate to Source Voltage



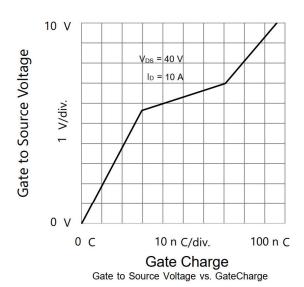


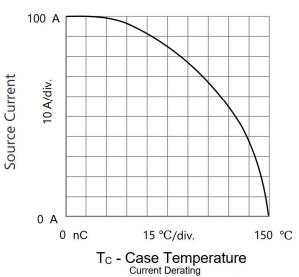


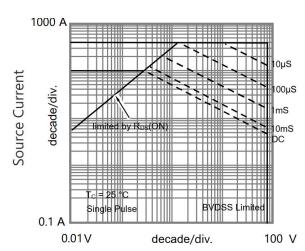




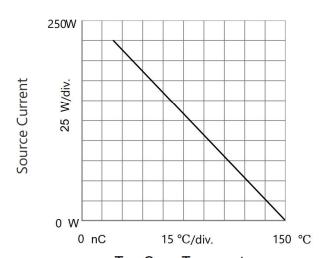
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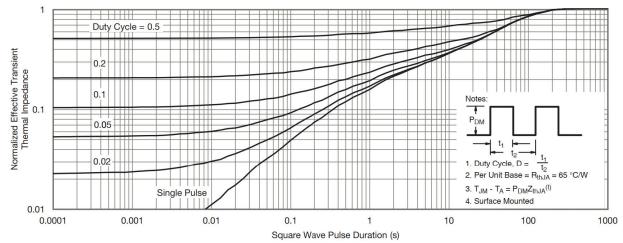




Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



 $T_{C} \textbf{ - Case Temperature}_{\text{Current Derating}}$



Normalized Thermal Transient Impedance, Junction-to-Ambient



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